

ABSTRACT OF THE DISCLOSURE

PECVD MICROCRYSTALLINE SILICON GERMANIUM (SiGe)

Embodiments of the present invention generally relate to methods for forming a SiGe layer. In one embodiment, a seed SiGe layer is first formed using plasma enhanced chemical vapor deposition (PECVD), and a bulk SiGe layer is formed directly on the PECVD seed layer also using PECVD.

Figure 2